

IGBT MODULE

GAE100BA60



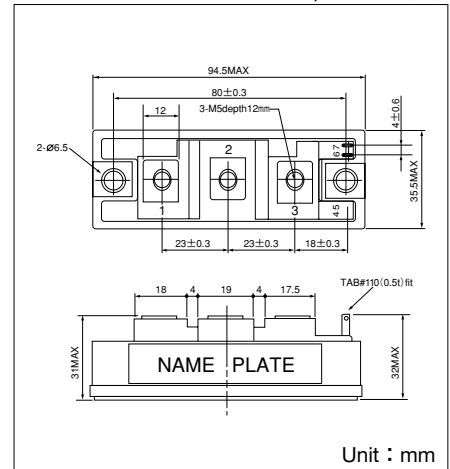
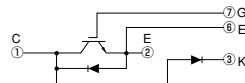
UL;E76102 (M)

SanRex IGBT Module **GAE100BA60** is designed for high speed, high current switching applications. This Module is electrically isolated and contains IGBT connected with clamp diode in series, soft recovery diode ($t_{rr}=0.1 \mu s$) reverse connected across IGBT.

- $I_C=100A$ $V_{CES}=600V$
- $V_{CE(sat)} = 2.3V$ Typ
- $t_f=0.10 \mu s$ Typ
- Soft recovery diode

(Applications)

Brake for motor control (chopper)



Unit : mm

Maximum Ratings

($T_j=25^\circ C$ unless otherwise specified)

Symbol	Item		Conditions	Ratings		Unit
				GAE100BA60		
V_{CES}	Collector-Emitter Voltage		with gate terminal shorted to emitter	600		V
V_{GES}	Gate-Emitter Voltage		with collector shorted to emitter	± 20		V
I_C	Collector Current	DC		100		A
I_{CP}		Pulse (1 ms)		200		
$-I_C$	Reverse Collector Current			100		A
P_C	Total Power Dissipation		$T_c=25^\circ C$	400		W
T_j	Junction Temperature			150		$^\circ C$
T_{stg}	Storage Temperature			-40 to +125		$^\circ C$
V_{ISO}	Isolation Voltage (R.M.S.)		A.C. 1 minute	2500		V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)		N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)		
	Mass		Typical Value	210		g

Electrical Characteristics

Symbol	Item		Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{GES}	Gate Leakage Current		$V_{GE}=\pm 20V, V_{CE}=0V$			± 500	nA
I_{CES}	Collector Cut-Off Current		$V_{CE}=600V, V_{GE}=0V$			1.0	mA
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage		$V_{GE}=0V, I_C=1mA$	600			V
$V_{GE(th)}$	Gate Threshold Voltage		$V_{CE}=10V, I_C=10mA$	3.0		7.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=100A, V_{GE}=15V$		2.3	2.8	V
C_{ies}	Input Capacitance		$V_{CE}=10V, V_{GE}=0V, f=1MHz$		7	10	nF
t_r	Switching Time	Rise Time	$I_C=100A, V_{GE}=+15V/-5V$ $V_{CC}=300V, R_G=6\Omega$		0.10	0.20	μs
$t_{d(on)}$		Turn-on Delay Time			0.20	0.40	
t_f		Fall Time			0.10	0.20	
$t_{d(off)}$		Turn-off Delay Time			0.40	0.80	
V_{ECS}	Emitter-Collector Voltage		$-I_C=100A, V_{GE}=0V$		2.00	2.80	V
t_{rr}	Reverse Recovery Time		$-I_C=100A, V_{GE}=-10V, di/dt=200A/\mu s$		0.1	0.15	μs
$R_{th(j-c)}$	Thermal Resistance		IGBT-Case			0.31	$^\circ C/W$
			Diode-Case			0.55	
V_{FM}	Forward Voltage Drop		$I_F=100A, \text{At Clamp Diode}$		2.00	2.80	V
t_{rr}	Reverse Recovery Time		$I_F=100A, di_F/dt=-200A/\mu s, \text{At Clamp Diode}$		0.1	0.15	μs
$R_{th(j-c)}$	Thermal Resistance		Junction-Case, At Clamp Diode			0.55	$^\circ C/W$

